09/176315

## ABSTRACT OF THE DISCLOSURE

A semiconductor device including a transistor having an SOI structure the operating speed of which is not affected is provided. A MOS transistor having the SOI structure is formed which satisfies R · C · f < 1 where C is a gate capacitance (F), R is a body resistance (Ω), f is a clock operating frequency (Hz), and f ≥ 500 MHz.